

In the Specification:

Please delete paragraph [0010] of the specification and insert the following paragraph [0010].

[0010] FIG. 1 is a longitudinal sectional view of the etching apparatus of a first embodiment, as viewed from the front surface thereof;
FIG. 2 is a longitudinal sectional view of the etching apparatus of the first embodiment, as viewed from the left side surface thereof;
FIG. 3(a) is a longitudinal sectional view of the left support arm 60 and left bracket 62, FIG. 3(b) is a longitudinal sectional view of the right support arm 70 and right bracket 72 of the first embodiment;
FIG. 4(a) is a longitudinal sectional view of the barrel of the first embodiment.
FIG. 4(b) is an enlarged view of section A shown in FIG. 1;
FIG. 5 is a longitudinal sectional view of the etching apparatus of a second embodiment, as viewed from the front surface thereof;
FIG. 6(a) is a longitudinal sectional view of the left support arm 160 and left bracket 162, and FIG. 6(b) is a longitudinal sectional view of the right support arm 170 and right bracket 172 of the second embodiment;
FIG. 7(a) is a longitudinal sectional view of the barrel of the second embodiment. FIG. 7(b) is a B-B' sectional view of FIG. 7(a);
~~FIG. 8 is a modification example of the cell plate that can be used in accordance with the present invention. Fig. 8(a) is an embodiment of the subject invention showing a cell plate with a large orifice in the middle. Fig. 8(b) is an embodiment of the subject invention showing a cell plate with a plurality of thin rectangular plates arranged in a row;~~
FIGS. 9(a)-9(c) show SFQR of the wafers after etching that was found, averaged, and visualized separately for the cases where the cell plate was larger than the wafer, smaller than the wafer, and of about the same size as the wafer;

FIGS. 10(a)-10(d) show data obtained when etching was conducted on 25 wafers by using the conventional etching apparatus and sampling was conducted from the 25 etched wafers;

FIGS. 11(a)-11(d) show data obtained when etching was conducted on 20 wafers by using the etching apparatus employing the present invention and sampling was conducted from the 20 etched wafers; and

FIG. 12 is a longitudinal sectional view of the conventional etching apparatus, as viewed from the front surface thereof.